

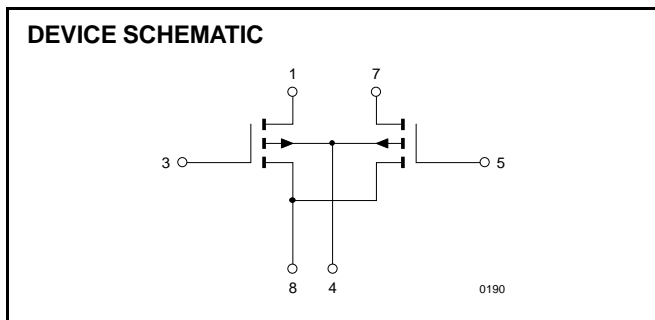
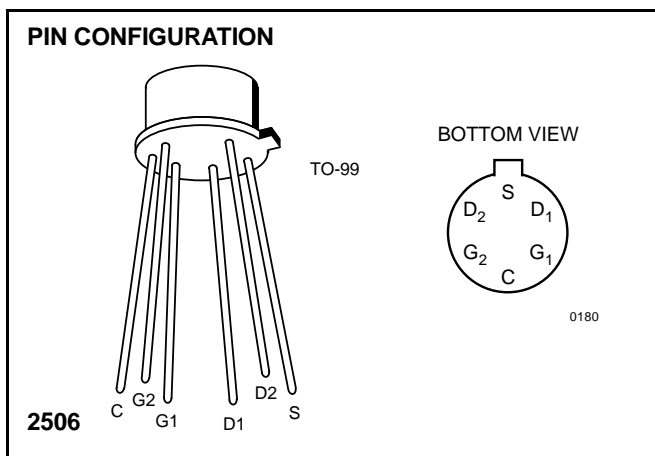
Monolithic Dual P-Channel Enhancement Mode MOSFET General Purpose Amplifier



3N165 / 3N166

FEATURES

- Very High Impedance
- High Gate Breakdown
- Low Capacitance



ABSOLUTE MAXIMUM RATINGS (Note 1)

($T_A = 25^\circ\text{C}$ unless otherwise specified)

Drain-Source or Drain-Gate Voltage (Note 2)

3N165	40V
3N166	30V

Transient Gate-Source Voltage (Note 3) ± 125

Gate-Gate Voltage $\pm 80\text{V}$

Drain Current (Note 2) 50mA

Storage Temperature -65°C to $+200^\circ\text{C}$

Operating Temperature -55°C to $+150^\circ\text{C}$

Lead Temperature (Soldering, 10sec) $+300^\circ\text{C}$

Power Dissipation

One Side 300mW

Both Sides 525mW

Total Derating above 25°C 4.2mW/ $^\circ\text{C}$

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

Part	Package	Temperature Range
3N165-66	Hermetic TO-99	-55°C to $+150^\circ\text{C}$
X3N165-66	Sorted Chips in Carriers	-55°C to $+150^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ and $V_{BS} = 0$ unless otherwise specified)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
I_{GSSR}	Gate Reverse Leakage Current		10	pA	$V_{GS} = 40\text{V}$
I_{GSSF}	Gate Forward Leakage Current		-10		$V_{GS} = -40\text{V}$
I_{DSS}	Drain to Source Leakage Current		-200		$V_{DS} = -20\text{V}$
I_{SDS}	Source to Drain Leakage Current		-400		$V_{SD} = -20\text{V}, V_{DB} = 0$
$I_{D(on)}$	On Drain Current	-5	-30	mA	$V_{DS} = -15\text{V}, V_{GS} = -10\text{V}$
$V_{GS(th)}$	Gate Source Threshold Voltage	-2	-5	V	$V_{DS} = -15\text{V}, I_D = -10\mu\text{A}$
$V_{GS(th)}$	Gate Source Threshold Voltage	-2	-5		$V_{DS} = V_{GS}, I_D = -10\mu\text{A}$
$r_{DS(on)}$	Drain Source ON Resistance		300	ohms	$V_{GS} = -20\text{V}, I_D = -100\mu\text{A}$

ELECTRICAL CHARACTERISTICS (Continued) ($T_A = 25^\circ\text{C}$ and $V_{BS} = 0$ unless otherwise specified)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
g_{fs}	Forward Transconductance	1500	3000	μS	$V_{DS} = -15\text{V}$, $I_D = -10\text{mA}$, $f = 1\text{kHz}$
g_{os}	Output Admittance		300		
C_{iss}	Input Capacitance		3.0	pF	$V_{DS} = -15\text{V}$, $I_D = -10\text{mA}$, $f = 1\text{MHz}$ (Note 4)
C_{rss}	Reverse Transfer Capacitance		0.7		
C_{oss}	Output Capacitance		3.0		
$R_E(Y_{fs})$	Common Source Forward Transconductance	1200		μS	$V_{DS} = -15\text{V}$, $I_D = -10\text{mA}$, $f = 100\text{MHz}$ (Note 4)

MATCHING CHARACTERISTICS 3N165

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
Y_{fs1} / Y_{fs2}	Forward Transconductance Ratio	0.90	1.0		$V_{DS} = -15\text{V}$, $I_D = -500\mu\text{A}$, $f = 1\text{kHz}$
V_{GS1-2}	Gate Source Threshold Voltage Differential		100	mV	$V_{DS} = -15\text{V}$, $I_D = -500\mu\text{A}$
$\frac{\Delta V_{GS1-2}}{\Delta T}$	Gate Source Threshold Voltage Differential Change with Temperature		100	$\mu\text{V}/^\circ\text{C}$	$V_{DS} = -15\text{V}$, $I_A = -500\mu\text{A}$ $T_A = -55^\circ\text{C}$ to $+25^\circ\text{C}$

- NOTES:**
1. See handling precautions on 3N170 data sheet.
 2. Per transistor.
 3. Devices must not be tested at $\pm 125\text{V}$ more than once, nor longer than 300ms.
 4. For design reference only, not 100% tested.